

# GTM ELECTRONICS

## SOT-26 POWER MOSFETS

Part No.	BVDSS(V)	RDS(ON) Max(mΩ)			Qg(nC) Typ.	ID(A)	PD(W)
		VGS@10V	VGS@4.5V	VGS@2.5V			
N- channel							
GT2602	20	30	34	50	8.7	6.3	2
GT6924E		-	600	850	1.3	1	0.9
GT2604	30	45	65	-	6	5.5	2
GT6301K		1000	2000	3000(2.7v)	1	0.64	1.2
GT2610	60	90	120	-	6	3	2
Dual N- channel							
GT2622	50	1800	3200	-	1	0.52	0.8
P- channel							
GT2603	-20	53	65	120	10.6	-5	2
GT2605	-30	80	120	-	5.5	-4	2
Dual P- channel							
GT2623	-30	170	280	-	2.8	-2	1.2
GT2625		135	185	265	4	-2.3	1.2
Complementary N-P channel							
GT2531	16	-	58	70	7	3.5	1.14
	-16	-	125	155	6	-2.5	
GT3585	20	-	75	125	4	3.5	1.14
	-20	120	160	300	5	-2.5	
GT2530	30	72	125	-	3	3.3	1.14
	-30	150	280	-	3	-2.3	

## TSOP-6 POWER MOSFETS

Part No.	BVDSS(V)	RDS(ON) Max(mΩ)			Qg(nC) Typ.	ID(A)	PD(W)
		VGS@10V	VGS@4.5V	VGS@2.5V			
N- channel							
GTT2602	20	30	34	50	8.7	6.3	2
GTT2604		45	65	-	6	5.5	2
GTT3434	30	-	34	50	8	6.1	1.14
GTT6301K		1000	2000	3000(2.7v)	1	0.64	1.2
GTT2610	60	90	120	-	6	3	2
Dual N- channel							
GTT8205S	20	-	28	38	23	6	1.14
GTT8209E		21	24	32	9.3	7	1.2
GTT2622	50	1800	3200	-	1	0.52	0.8
P- channel							
GTT2603	-20	53	65	120	10.6	-5	2
GTT2605	-30	80	120	-	5.5	-4	2
GTT3455		100	170	-	5.5	-4	2
Dual P- channel							
GTT2623	-30	170	280	-	2.8	-2	1.2
GTT2625		135	185	265	4	-2.3	1.2
Complementary N-P channel							
GTT3585	20	-	75	125	4	3.5	1.14
	-20	120	160	300	5	-2.5	

量産	未量産	有様品	工程實驗未産出
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